



Mr. JANG WON JUN

School of Advanced Materials Science and Engineering,
Sungkyunkwan University

Advanced R&D Center, Wonik IPS Co., Republic of
Korea



Education

Materials Science & Engineering KOREA University, Seoul, Korea

B.S. in Materials Science & Engineering (1988 ~ 1991)

M.S. in Materials Science & Engineering (1992 ~ 1993)

Advanced Materials Science and Engineering, Sungkyunkwan Univ., Seoul, Korea

D.S. in Advanced Materials Science and Engineering (2019 ~ Current)

R&D Center, Samsung Electronics (1994 ~ 2017)

- . Successfully developed MOCVD **Ta₂O₅** Capacitor Module for 1G DRAM
: Received the "**Proud Samsung Award**" from SEC chairman Kun-Hee Lee
- . Successfully researched and developed the world first **Plasma Nitridation**
(the origin of DPN, SPA, MMT)
- . Developed **RNC**(Radical oxidation/NO anneal/Clean Oxidation) Tunnel Oxide
- . Key Development & Mass Production Transferred List
: Spike RTA, Laser Anneal, Flash RTP etc.

Advanced R&D Center, Wonik IPS (2017 ~ Current)

- . Successfully developed High-/Low- Pressure Swing Anneal Equipment (first ever developed)
- : Received the "**Proud Wonik Award**" from Wonik chairman Yong-Han Lee